CGD985LC

1 GHz, 25 dB gain GaAs low current power doubler Rev. 1 — 10 March 2014 Produc

Product data sheet

1. **Product profile**

1.1 General description

Hybrid amplifier module in a SOT115AE package, operating at a supply voltage of 24 V Direct Current (DC), employing Heterojunction Field Effect Transistor (HFET) GaAs dies.

1.2 Features and benefits

- Low power consumption
- Excellent linearity
- Optimized for PAL D loading
- Extremely low noise
- Excellent return loss properties
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Adjustable supply current

1.3 Applications

 CATV systems operating in the 40 MHz to 1 GHz frequency range using PAL D channel conditions.

1.4 Quick reference data

Quick reference data

Bandwidth 40 MHz to 1003 MHz; V_B = 24 V (DC); Z_S = Z_L = 75 Ω ; T_{mb} = 35 °C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		22.5	23.5	24.5	dB
		f = 1003 MHz		24	25	26	dB
СТВ	composite triple beat	V _o = 48 dBmV at 862 MHz	[1][2]	-	-65	-59	dBc
CSO	composite second-order distortion	V _o = 48 dBmV at 862 MHz	[1][2]	-	-70	-60	dBc
I _{tot}	total current	pin 4 not connected	[3]	345	365	385	mΑ
		pin 4 connected to ground	[3]	-	315	-	mA

^{[1] 98} PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_0 till 862 MHz.

- [2] pin 4 not connected.
- [3] Direct Current (DC).



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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input		S
2, 3	common	1 579	1 4 5 9
4	I _{CC} adjust [1]		>
5	+V _B		2378
7, 8	common		aaa-011041
9	output		

^[1] The total supply current can be adjusted by pin 4. Grounding of pin 4 gives the lowest supply current while floating of pin 4 gives the maximum supply current.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
CGD985LC	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 × 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads	SOT115AE		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_B	supply voltage		-	30	V
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
I _I	input current	on I _{CC} adjust (pin 4)	-10	0	mA
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

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5. Characteristics

 Table 5.
 Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \degree C$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		22.5	23.5	24.5	dB
		f = 1003 MHz		24	25	26	dB
SL _{sl}	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.7	-	2.2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	0.8	dB
RLin	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		15	-	-	dB
RL _{out}	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
NF	noise figure	f = 50 MHz		-	5.0	6.0	dB
		f = 1003 MHz		-	5.5	6.5	dB
Pin 4 not	connected						
I _{tot}	total current		[3]	345	365	385	mA
98 PAL D	channels						
СТВ	composite triple beat	V _o = 48 dBmV at 862 MHz	[4]	-	-65	-59	dBc
CSO	composite second-order distortion	V _o = 48 dBmV at 862 MHz	[4]	-	-70	-60	dBc
Xmod	cross modulation	V _o = 48 dBmV at 862 MHz	[4][5]	-	-60	-	dB
59 PAL D	channels + 75 digital channels						
СТВ	composite triple beat	V _o = 58.5 dBmV at 1003 MHz	[6]	-	-72	-	dBc
CSO	composite second-order distortion	V _o = 58.5 dBmV at 1003 MHz	[6]	-	-75	-	dBc
Xmod	cross modulation	V _o = 58.5 dBmV at 1003 MHz	[5][6]	-	-67	-	dB
CCN	carrier-to-composite noise	V _o = 58.5 dBmV at 1003 MHz	[6]	-	62	-	dBc

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 Table 5.
 Characteristics ...continued

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \degree$ C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Pin 4 conr	nected to ground					
I _{tot}	total current	[3]	-	315	-	mA
98 PAL D	channels					
СТВ	composite triple beat	$V_0 = 48 \text{ dBmV at } 862 \text{ MHz}$	-	-58	-	dBc
CSO	composite second-order distortion	$V_0 = 48 \text{ dBmV at } 862 \text{ MHz}$	-	-69	-	dBc
59 PAL D	channels + 75 digital channels					
СТВ	composite triple beat	$V_0 = 58.5 \text{ dBmV at } 1003 \text{ MHz}$ [6]	-	-64	-	dBc
CSO	composite second-order distortion	$V_0 = 58.5 \text{ dBmV at } 1003 \text{ MHz}$ [6]	-	-64	-	dBc
CCN	carrier-to-composite noise	$V_0 = 58.5 \text{ dBmV at } 1003 \text{ MHz}$ [6]	-	55	-	dBc

- [1] G_p at 1003 MHz minus G_p at 40 MHz.
- [2] Flatness is defined as peak deviation to straight line.
- [3] Direct Current (DC).
- [4] 98 PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_0 till 862 MHz.
- [5] Measured at 55.25 MHz.
- [6] 59 PAL D channels [f = 49.75 MHz to 543.25 MHz] + 75 digital channels [f = 555.25 MHz to 1003 MHz] (-10 dB offset); 13.5 dB tilt extrapolated to 1003 MHz.

6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 8 gold-plated in-line leads

SOT115AE

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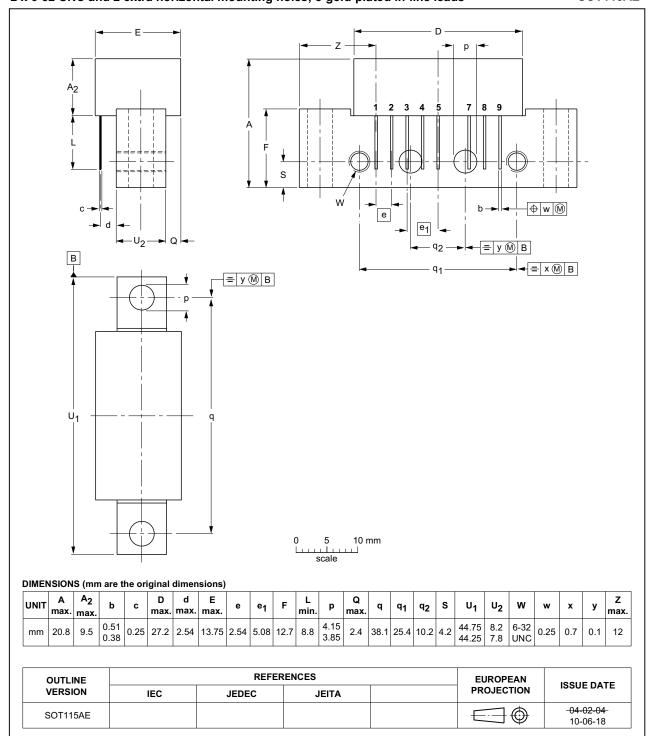


Fig 1. Package outline SOT115AE

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7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
PAL D	Phase Alternate Line standard D
UNC	UNified Coarse

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD985LC v.1	20140310	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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